

Miao Xu

List of Publications by Year in descending order

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108
papers

6,005
citations

218381

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69108

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108
all docs

108
docs citations

108
times ranked

6999
citing authors

#	ARTICLE	IF	CITATIONS
1	Enhanced power-conversion efficiency in polymer solar cells using an inverted device structure. <i>Nature Photonics</i> , 2012, 6, 591-595.	15.6	3,583
2	Manipulation of Charge and Exciton Distribution Based on Blue Aggregation-Induced Emission Fluorophors: A Novel Concept to Achieve High-Performance Hybrid White Organic Light-Emitting Diodes. <i>Advanced Functional Materials</i> , 2016, 26, 776-783.	7.8	194
3	Manipulation of exciton distribution for high-performance fluorescent/phosphorescent hybrid white organic light-emitting diodes. <i>Journal of Materials Chemistry C</i> , 2017, 5, 7668-7683.	2.7	95
4	High-performance doping-free hybrid white organic light-emitting diodes: The exploitation of ultrathin emitting nanolayers ($\leq 1\text{ nm}$). <i>Nano Energy</i> , 2016, 26, 26-36.	8.2	88
5	A flexible AMOLED display on the PEN substrate driven by oxide thin-film transistors using anodized aluminium oxide as dielectric. <i>Journal of Materials Chemistry C</i> , 2014, 2, 1255-1259.	2.7	84
6	High performance indium-zinc-oxide thin-film transistors fabricated with a back-channel-etch-technique. <i>Applied Physics Letters</i> , 2011, 99, .	1.5	80
7	Full-color quantum dots active matrix display fabricated by ink-jet printing. <i>Science China Chemistry</i> , 2017, 60, 1349-1355.	4.2	67
8	Enhanced moisture barrier performance for ALD-encapsulated OLEDs by introducing an organic protective layer. <i>Journal of Materials Chemistry C</i> , 2017, 5, 4017-4024.	2.7	66
9	High-Performance Doping-Free Hybrid White OLEDs Based on Blue Aggregation-Induced Emission Luminogens. <i>ACS Applied Materials & Interfaces</i> , 2017, 9, 34162-34171.	4.0	66
10	Low-Voltage High-Stability Indium-Zinc Oxide Thin-Film Transistor Gated by Anodized Neodymium-Doped Aluminum. <i>IEEE Electron Device Letters</i> , 2012, 33, 827-829.	2.2	54
11	High Mobility Amorphous Indium-Gallium-Zinc-Oxide Thin-Film Transistor by Aluminum Oxide Passivation Layer. <i>IEEE Electron Device Letters</i> , 2017, 38, 879-882.	2.2	54
12	Extremely stable-color flexible white organic light-emitting diodes with efficiency exceeding 100 lm W^{-1} . <i>Journal of Materials Chemistry C</i> , 2014, 2, 9836-9841.	2.7	48
13	Harnessing charge and exciton distribution towards extremely high performance: the critical role of guests in single-emitting-layer white OLEDs. <i>Materials Horizons</i> , 2015, 2, 536-544.	6.4	48
14	Efficient hybrid white organic light-emitting diodes with extremely long lifetime: the effect of n-type interlayer. <i>Scientific Reports</i> , 2014, 4, 7198.	1.6	42
15	Role of Rare Earth Ions in Anodic Gate Dielectrics for Indium-Zinc-Oxide Thin-Film Transistors. <i>Journal of the Electrochemical Society</i> , 2012, 159, H502-H506.	1.3	39
16	Doping-free tandem white organic light-emitting diodes. <i>Science Bulletin</i> , 2017, 62, 1193-1200.	4.3	37
17	Investigation and optimization of each organic layer: A simple but effective approach towards achieving high-efficiency hybrid white organic light-emitting diodes. <i>Organic Electronics</i> , 2014, 15, 926-936.	1.4	36
18	Influence of Source and Drain Contacts on the Properties of Indium-Gallium-Zinc-Oxide Thin-Film Transistors based on Amorphous Carbon Nanofilm as Barrier Layer. <i>ACS Applied Materials & Interfaces</i> , 2015, 7, 3633-3640.	4.0	35

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19	Very-High Color Rendering Index Hybrid White Organic Light-Emitting Diodes with Double Emitting Nanolayers. <i>Nano-Micro Letters</i> , 2014, 6, 335-339.	14.4	34
20	Trap-Assisted Enhanced Bias Illumination Stability of Oxide Thin Film Transistor by Praseodymium Doping. <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 5232-5239.	4.0	34
21	Regulating charges and excitons in simplified hybrid white organic light-emitting diodes: The key role of concentration in single dopant host-guest systems. <i>Organic Electronics</i> , 2014, 15, 2616-2623.	1.4	32
22	Realization of highly-dense Al ₂ O ₃ gas barrier for top-emitting organic light-emitting diodes by atomic layer deposition. <i>RSC Advances</i> , 2015, 5, 104613-104620.	1.7	32
23	Influence of source and drain contacts on the properties of the indium-zinc oxide thin-film transistors based on anodic aluminum oxide gate dielectrics. <i>Journal of Applied Physics</i> , 2011, 110, .	1.1	30
24	Direct patterning of silver electrodes with 2.4 μm channel length by piezoelectric inkjet printing. <i>Journal of Colloid and Interface Science</i> , 2017, 487, 68-72.	5.0	30
25	Effect of ITO Serving as a Barrier Layer for Cu Electrodes on Performance of a-IGZO TFT. <i>IEEE Electron Device Letters</i> , 2018, 39, 504-507.	2.2	30
26	An ideal host-guest system to accomplish high-performance greenish yellow and hybrid white organic light-emitting diodes. <i>Organic Electronics</i> , 2015, 27, 29-34.	1.4	28
27	High-performance back-channel-etched thin-film transistors with amorphous Si-incorporated SnO ₂ active layer. <i>Applied Physics Letters</i> , 2016, 108, .	1.5	25
28	Comprehensive Study on the Electron Transport Layer in Blue Fluorescent Organic Light-Emitting Diodes. <i>ECS Journal of Solid State Science and Technology</i> , 2013, 2, R258-R261.	0.9	24
29	Effects of Etching Residue on Positive Shift of Threshold Voltage in Amorphous Indium-Zinc-Oxide Thin-Film Transistors Based on Back-Channel-Etch Structure. <i>IEEE Transactions on Electron Devices</i> , 2014, 61, 92-97.	1.6	23
30	Simultaneous achievement of low efficiency roll-off and stable color in highly efficient single-emitting-layer phosphorescent white organic light-emitting diodes. <i>Journal of Materials Chemistry C</i> , 2014, 2, 5870-5877.	2.7	23
31	Method for Fabricating Amorphous Indium-Zinc-Oxide Thin-Film Transistors With Copper Source and Drain Electrodes. <i>IEEE Electron Device Letters</i> , 2015, 36, 342-344.	2.2	23
32	A Low-Power High-Stability Flexible Scan Driver Integrated by IZO TFTs. <i>IEEE Transactions on Electron Devices</i> , 2016, 63, 1779-1782.	1.6	23
33	Light extraction of flexible OLEDs based on transparent polyimide substrates with 3-D photonic structure. <i>Organic Electronics</i> , 2017, 44, 225-231.	1.4	23
34	Highly efficient red phosphorescent organic light-emitting diodes based on solution processed emissive layer. <i>Journal of Luminescence</i> , 2013, 142, 35-39.	1.5	22
35	High-Performance Hybrid White Organic Light-Emitting Diodes Comprising Ultrathin Blue and Orange Emissive Layers. <i>Applied Physics Express</i> , 2013, 6, 122101.	1.1	22
36	Performance improvement of oxide thin-film transistors with a two-step-annealing method. <i>Solid-State Electronics</i> , 2014, 91, 9-12.	0.8	22

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37	Power Consumption Model for AMOLED Display Panel Based on 2T-1C Pixel Circuit. <i>Journal of Display Technology</i> , 2016, 12, 1064-1069.	1.3	22
38	Realization of Al ₂ O ₃ /MgO laminated structure at low temperature for thin film encapsulation in organic light-emitting diodes. <i>Nanotechnology</i> , 2016, 27, 494003.	1.3	22
39	TFT-Directed Electroplating of RGB Luminescent Films without a Vacuum or Mask toward a Full-Color AMOLED Pixel Matrix. <i>ACS Applied Materials & Interfaces</i> , 2018, 10, 17519-17525.	4.0	22
40	Effects of praseodymium doping on the electrical properties and aging effect of InZnO thin-film transistor. <i>Journal of Materials Science</i> , 2019, 54, 14778-14786.	1.7	22
41	Analytical Extraction Method for Density of States in Metal Oxide Thin-Film Transistors by Using Low-Frequency Capacitance-Voltage Characteristics. <i>Journal of Display Technology</i> , 2016, 12, 888-891.	1.3	21
42	A High-Reliability Gate Driver Integrated in Flexible AMOLED Display by IZO TFTs. <i>IEEE Transactions on Electron Devices</i> , 2017, 64, 1991-1996.	1.6	21
43	An AC Driving Pixel Circuit Compensating for TFTs Threshold-Voltage Shift and OLED Degradation for AMOLED. <i>Journal of Display Technology</i> , 2013, 9, 572-576.	1.3	20
44	Damage-Free Back Channel Wet-Etch Process in Amorphous Indium-Zinc-Oxide Thin-Film Transistors Using a Carbon-Nanofilm Barrier Layer. <i>ACS Applied Materials & Interfaces</i> , 2014, 6, 11318-11325.	4.0	20
45	Efficient single-emitting layer hybrid white organic light-emitting diodes with low efficiency roll-off, stable color and extremely high luminance. <i>Journal of Industrial and Engineering Chemistry</i> , 2015, 30, 85-91.	2.9	20
46	High mobility flexible polymer thin-film transistors with an octadecyl-phosphonic acid treated electrochemically oxidized alumina gate insulator. <i>Journal of Materials Chemistry C</i> , 2015, 3, 7062-7066.	2.7	20
47	Effect of Post Treatment For Cu-Cr Source/Drain Electrodes on a-IGZO TFTs. <i>Materials</i> , 2016, 9, 623.	1.3	20
48	Improving Thermal Stability of Solution-Processed Indium Zinc Oxide Thin-Film Transistors by Praseodymium Oxide Doping. <i>ACS Applied Materials & Interfaces</i> , 2018, 10, 28764-28771.	4.0	20
49	A Highly Stable Biside Gate Driver Integrated by IZO TFTs. <i>IEEE Transactions on Electron Devices</i> , 2014, 61, 3335-3338.	1.6	19
50	Fabrication of Flexible Amorphous Indium-Gallium-Zinc-Oxide Thin-Film Transistors by a Chemical Vapor Deposition-Free Process on Polyethylene Naphthalate. <i>ECS Journal of Solid State Science and Technology</i> , 2014, 3, Q3035-Q3039.	0.9	19
51	High-performance hybrid white organic light-emitting diodes employing p-type interlayers. <i>Journal of Industrial and Engineering Chemistry</i> , 2015, 27, 240-244.	2.9	19
52	A Low-Power Ring Oscillator Using Pull-Up Control Scheme Integrated by Metal-Oxide TFTs. <i>IEEE Transactions on Electron Devices</i> , 2017, 64, 4946-4951.	1.6	19
53	Effect of Al ₂ O ₃ Passivation Layer and Cu Electrodes on High Mobility of Amorphous IZO TFT. <i>IEEE Journal of the Electron Devices Society</i> , 2018, 6, 733-737.	1.2	19
54	Impact of Deposition Temperature of the Silicon Oxide Passivation on the Performance of Indium Zinc Oxide Thin-Film Transistors. <i>Japanese Journal of Applied Physics</i> , 2012, 51, 076501.	0.8	19

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55	Gate bias stress stability under light irradiation for indium zinc oxide thin-film transistors based on anodic aluminium oxide gate dielectrics. <i>Journal Physics D: Applied Physics</i> , 2011, 44, 455102.	1.3	18
56	A novel nondestructive testing method for amorphous Si ϵ Sn ϵ O films. <i>Journal Physics D: Applied Physics</i> , 2016, 49, 505102.	1.3	18
57	Improvement of Mobility and Stability in Oxide Thin-Film Transistors Using Triple-Stacked Structure. <i>IEEE Electron Device Letters</i> , 2016, 37, 57-59.	2.2	18
58	High-Resolution Flexible AMOLED Display Integrating Gate Driver by Metal ϵ Oxide TFTs. <i>IEEE Electron Device Letters</i> , 2018, 39, 1660-1663.	2.2	18
59	Mobility Enhancement in Amorphous In-Ga-Zn-O Thin-Film Transistor by Induced Metallic in Nanoparticles and Cu Electrodes. <i>Nanomaterials</i> , 2018, 8, 197.	1.9	18
60	The effect of charge transfer transition on the photostability of lanthanide-doped indium oxide thin-film transistors. <i>Communications Materials</i> , 2021, 2, .	2.9	18
61	Investigation on spacers and structures: A simple but effective approach toward high-performance hybrid white organic light emitting diodes. <i>Synthetic Metals</i> , 2013, 184, 5-9.	2.1	16
62	Flexible organic field-effect transistors with high-reliability gate insulators prepared by a room-temperature, electrochemical-oxidation process. <i>RSC Advances</i> , 2015, 5, 15695-15699.	1.7	16
63	High-mobility ZrInO thin-film transistor prepared by an all-DC-sputtering method at room temperature. <i>Scientific Reports</i> , 2016, 6, 25000.	1.6	16
64	Effect of Intrinsic Stress on Structural and Optical Properties of Amorphous Si-Doped SnO ₂ Thin-Film. <i>Materials</i> , 2017, 10, 24.	1.3	15
65	High-Performance and Flexible Neodymium-Doped Oxide Semiconductor Thin-Film Transistors With Copper Alloy Bottom-Gate Electrode. <i>IEEE Electron Device Letters</i> , 2018, 39, 839-842.	2.2	15
66	Simplified hybrid white organic light-emitting diodes with efficiency/efficiency roll-off/color rendering index/color-stability trade-off. <i>Physica Status Solidi - Rapid Research Letters</i> , 2014, 8, 719-723.	1.2	14
67	The effect of spacer in hybrid white organic light emitting diodes. <i>Science Bulletin</i> , 2014, 59, 3090-3097.	1.7	14
68	Reduced contact resistance of a-IGZO thin film transistors with inkjet-printed silver electrodes. <i>Journal Physics D: Applied Physics</i> , 2018, 51, 165103.	1.3	14
69	Low-Power Bi-Side Scan Driver Integrated by IZO TFTs Including a Clock-Controlled Inverter. <i>Journal of Display Technology</i> , 2014, 10, 523-525.	1.3	13
70	High ϵ mobility flexible thin ϵ film transistors with a low ϵ temperature zirconium ϵ doped indium oxide channel layer. <i>Physica Status Solidi - Rapid Research Letters</i> , 2016, 10, 493-497.	1.2	13
71	A physics-based model of threshold voltage for amorphous oxide semiconductor thin-film transistors. <i>AIP Advances</i> , 2016, 6, .	0.6	11
72	A room temperature strategy towards enhanced performance and bias stability of oxide thin film transistor with a sandwich structure channel layer. <i>Applied Physics Letters</i> , 2017, 110, .	1.5	11

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73	All-Aluminum Thin Film Transistor Fabrication at Room Temperature. <i>Materials</i> , 2017, 10, 222.	1.3	11
74	Island-Like AZO/Al ₂ O ₃ Bilayer Channel Structure for Thin Film Transistors. <i>Advanced Materials Interfaces</i> , 2017, 4, 1700063.	1.9	10
75	Impact of Deposition Temperature of the Silicon Oxide Passivation on the Performance of Indium Zinc Oxide Thin-Film Transistors. <i>Japanese Journal of Applied Physics</i> , 2012, 51, 076501.	0.8	9
76	High reliability amorphous oxide semiconductor thin-film transistors gated by buried thick aluminum. <i>Physica Status Solidi - Rapid Research Letters</i> , 2012, 6, 403-405.	1.2	9
77	Highly stable amorphous indium-zinc-oxide thin-film transistors with back-channel wet-etch process. <i>Physica Status Solidi - Rapid Research Letters</i> , 2014, 8, 176-181.	1.2	9
78	Low-temperature, high-stability, flexible thin-film transistors with a novel Sc _x In _{1-x} O ₃ semiconductor. <i>Journal Physics D: Applied Physics</i> , 2016, 49, 24LT01.	1.3	9
79	24 th : Flexible AMOLED based on Oxide TFT with High Mobility. <i>Digest of Technical Papers SID International Symposium</i> , 2017, 48, 342-344.	0.1	8
80	High-Performance Back-Channel-Etch Thin-Film Transistors With Zinc Tin Oxide as Barrier Layer via Spray Coating. <i>IEEE Transactions on Electron Devices</i> , 2019, 66, 3854-3860.	1.6	8
81	Facilitation of transparent gas barrier using SiN _x /a-IZO lamination for organic light emitting diodes. <i>Organic Electronics</i> , 2015, 24, 57-64.	1.4	6
82	Indium-Gallium-Zinc-Oxide Thin-Film Transistors Based on Homojunctioned Structure Fabricated With a Self-Aligned Process. <i>Journal of Display Technology</i> , 2015, 11, 589-595.	1.3	6
83	A physics-based model of flat-band capacitance for metal oxide thin-film transistors. <i>AIP Advances</i> , 2018, 8, .	0.6	6
84	Dual Gate Indium-Zinc Oxide Thin-Film Transistors Based on Anodic Aluminum Oxide Gate Dielectrics. <i>IEEE Transactions on Electron Devices</i> , 2014, 61, 2448-2453.	1.6	5
85	Highly transparent and thermal-stable silver nanowire conductive film covered with ZnMgO by atomic-layer-deposition. <i>Journal of Physics and Chemistry of Solids</i> , 2017, 111, 328-334.	1.9	5
86	A low-power gate driver integrated by IZO-TFTs employing single negative power source. <i>Semiconductor Science and Technology</i> , 2018, 33, 065006.	1.0	5
87	A low-power D flip flop integrated by metal oxide thin film transistors employing internal feedback control. <i>Semiconductor Science and Technology</i> , 2018, 33, 115004.	1.0	5
88	Enhanced Negative-Bias Illumination Temperature Stability of Praseodymium-Doped InGaO Thin-Film Transistors. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2021, 218, 2000812.	0.8	5
89	<i>Letter:</i> A new compensation pixel circuit with metal oxide thin-film transistors for active-matrix organic light-emitting diode displays. <i>Journal of the Society for Information Display</i> , 2015, 23, 233-239.	0.8	4
90	Design of high speed gate driver employing IZO TFTs. <i>Displays</i> , 2015, 39, 93-99.	2.0	4

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91	Highly conductive AZO thin films obtained by rationally optimizing substrate temperature and oxygen partial pressure. <i>Molecular Crystals and Liquid Crystals</i> , 2017, 644, 190-196.	0.4	4
92	IZO Protected Silver Films Used as Anodes in Top-Emitting Organic LEDs. <i>ECS Journal of Solid State Science and Technology</i> , 2013, 2, R190-R195.	0.9	3
93	Low-Roughness and Easily-Etched Transparent Conducting Oxides with a Stack Structure of ITO and IZO. <i>ECS Journal of Solid State Science and Technology</i> , 2013, 2, R245-R248.	0.9	3
94	16.2: A 4.8-inch AMOLED Display Panel Driven by Stable Amorphous In-Zn-O Thin-Film Transistor. <i>Digest of Technical Papers SID International Symposium</i> , 2013, 44, 170-173.	0.1	3
95	20.4L: Late News Paper: A Flexible AMOLED Display on PEN Substrate Driven by Oxide Thin-Film Transistors. <i>Digest of Technical Papers SID International Symposium</i> , 2014, 45, 260-262.	0.1	3
96	High-speed low-power voltage-programmed driving scheme for AMOLED displays. <i>Journal of Semiconductors</i> , 2015, 36, 125005.	2.0	3
97	Letter: Solution-processed flexible zinc-tin oxide thin-film transistors on ultra-thin polyimide substrates. <i>Journal of the Society for Information Display</i> , 2016, 24, 211-215.	0.8	3
98	Manchester-encoded data transmission circuit integrated by metal-oxide TFTs suitable for 13.56-MHz radio-frequency identification tag application. <i>IET Circuits, Devices and Systems</i> , 2018, 12, 771-776.	0.9	3
99	A Semi-Analytical Extraction Method for Interface and Bulk Density of States in Metal Oxide Thin-Film Transistors. <i>Materials</i> , 2018, 11, 416.	1.3	3
100	A 256 Å— 256, 50- $\frac{1}{4}$ m Pixel Pitch OPD Image Sensor Based on an IZO TFT Backplane. <i>IEEE Sensors Journal</i> , 2021, 21, 20824-20832.	2.4	3
101	Optimization of carrier transport layer: A simple but effective approach toward achieving high efficiency all-solution processed InP quantum dot light emitting diodes. <i>Organic Electronics</i> , 2021, 96, 106256.	1.4	3
102	A scan driver including light emission control integrated by metal-oxide thin-film transistors. <i>Semiconductor Science and Technology</i> , 2021, 36, 025006.	1.0	3
103	Influence of passivation deposition on the performance of In-Zn-O thin-film transistors based on etch-stopper structure. <i>Materials Research Express</i> , 2014, 1, 036402.	0.8	2
104	A metal oxide TFT gate driver with a single negative power source employing a boosting module. <i>Journal of Information Display</i> , 2020, 21, 57-64.	2.1	2
105	An Analytical Frequency-Dependent Capacitance-Voltage Model for Metal Oxide Thin-Film Transistors. <i>IEEE Transactions on Electron Devices</i> , 2022, 69, 141-146.	1.6	2
106	Flexible amorphous oxide thin-film transistors on polyimide substrate for AMOLED. , 2014, , .		1
107	High performance and illumination stable In ₂ O ₃ nanofibers-based field effect transistors by doping praseodymium. <i>Surfaces and Interfaces</i> , 2022, 29, 101781.	1.5	1
108	15.2: Invited Paper: Back-Channel-Etch Thin Film Transistors with Zinc Tin Oxide as Barrier Layer via Spray Coating. <i>Digest of Technical Papers SID International Symposium</i> , 2019, 50, 152-152.	0.1	0